

# Yanbing Han

## List of Publications by Year in descending order

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19  
papers

531  
citations

687363

13  
h-index

794594

19  
g-index

19  
all docs

19  
docs citations

19  
times ranked

682  
citing authors

#	ARTICLE	IF	CITATIONS
1	Wide Band Gap Chalcogenide Semiconductors. <i>Chemical Reviews</i> , 2020, 120, 4007-4055.	47.7	246
2	Effects of silicon doping on the performance of tin oxide thin film transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 1010-1015.	1.8	36
3	Fabrication of 2D PdSe <sub>2</sub> /3D CdTe Mixed-Dimensional van der Waals Heterojunction for Broadband Infrared Detection. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 41791-41801.	8.0	30
4	Optoelectronic Properties of Strontium and Barium Copper Sulfides Prepared by Combinatorial Sputtering. <i>Chemistry of Materials</i> , 2017, 29, 8239-8248.	6.7	28
5	Combinatorial Tuning of Structural and Optoelectronic Properties in Cu Zn <sup>1-x</sup> S. <i>Matter</i> , 2019, 1, 862-880.	10.0	26
6	Characteristic of Bismuth-Doped Tin Oxide Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 1904-1909.	3.0	25
7	H <sub>2</sub> O adsorption on amorphous In-Ga-Zn-O thin-film transistors under negative bias stress. <i>Applied Physics Letters</i> , 2017, 111, .	3.3	23
8	Stabilization of wide band-gap p-type wurtzite MnTe thin films on amorphous substrates. <i>Journal of Materials Chemistry C</i> , 2018, 6, 6297-6304.	5.5	21
9	Influences of Nitrogen Doping on the Electrical Characteristics of Indium-Zinc-Oxide Thin Film Transistors. <i>IEEE Transactions on Device and Materials Reliability</i> , 2016, 16, 642-646.	2.0	16
10	H <sub>2</sub> O Induced Hump Phenomenon in Capacitance-Voltage Measurements of a-IGZO Thin-Film Transistors. <i>IEEE Transactions on Device and Materials Reliability</i> , 2016, 16, 20-24.	2.0	16
11	Enhancing the optical absorption of chalcogenide perovskite BaZrS <sub>3</sub> by optimizing the synthesis and post-processing conditions. <i>Journal of Solid State Chemistry</i> , 2022, 307, 122872.	2.9	15
12	Combinatorial Nitrogen Gradients in Sputtered Thin Films. <i>ACS Combinatorial Science</i> , 2018, 20, 436-442.	3.8	13
13	Zinc-Stabilized Manganese Telluride with Wurtzite Crystal Structure. <i>Journal of Physical Chemistry C</i> , 2018, 122, 18769-18775.	3.1	13
14	Effects of Nitrogen Doping on Performance of Amorphous SnSiO Thin Film Transistor. <i>Journal of Display Technology</i> , 2016, 12, 1560-1564.	1.2	10
15	Templated Growth of Metastable Polymorphs on Amorphous Substrates with Seed Layers. <i>Physical Review Applied</i> , 2020, 13, .	3.8	7
16	Asymmetric contact in tin bismuth oxide thin film transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600589.	1.8	2
17	Wurtzite materials in alloys of rock salt compounds. <i>Journal of Materials Research</i> , 2020, 35, 972-980.	2.6	2
18	High-throughput fabrication and semi-automated characterization of oxide thin film transistors. <i>Chinese Physics B</i> , 2020, 29, 018502.	1.4	1

#	ARTICLE	IF	CITATIONS
19	Solution processed amorphous gallium-incorporated tin oxide thin-film transistors. Japanese Journal of Applied Physics, 2020, 59, 050906.	1.5	1